



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



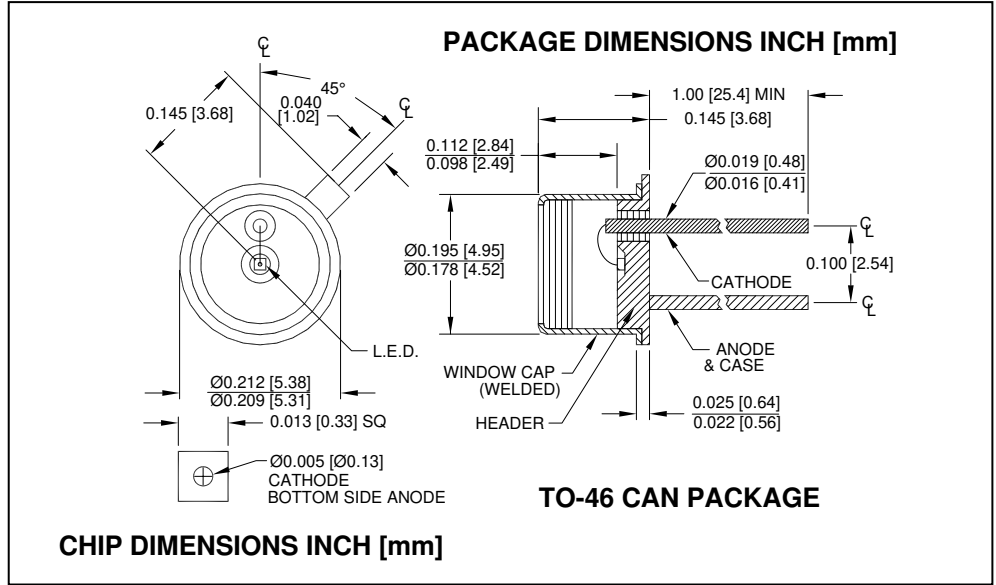
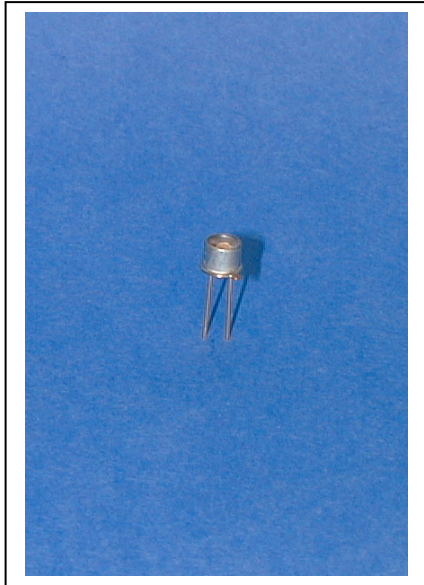
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FEATURES

- High output power
- High reliability
- Wide emission angle

DESCRIPTION

The **PDI-E801** is an 880 nm high power GaAlAs infrared emitter packaged in a hermetic TO-46 metal header with a flat window glass.

APPLICATIONS

- Photoelectric switches
- Optical encoders
- Infrared sources

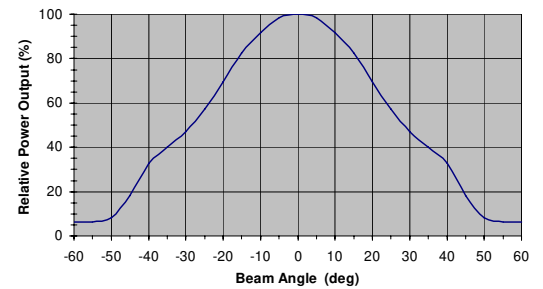


ABSOLUTE MAXIMUM RATING (TA)= 23°C UNLESS OTHERWISE NOTED

SYMBOL	PARAMETER	MIN	MAX	UNITS
P_d	Power Dissipation		160	mW
I_f	Continuous Forward Current		100	mA
I_p	Peak Forward Current		3.0	A
V_r	Reverse Voltage		5	V
T_{STG}	Storage Temperature	-55	+100	°C
T_O	Operating Temperature	-55	+100	°C
T_S	Soldering Temperature*		+240	°C

* 1/16 inch from case for 3 seconds max.

RADIATION PATTERN



ELECTRO-OPTICAL CHARACTERISTICS RATING (TA)= 23°C UNLESS OTHERWISE NOTED

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
P_o	Output Power	$I_f = 100$ mA	4	5.6		mW
V_f	Forward Voltage	$I_f = 100$ mA		1.5	1.9	V
V_r	Reverse Breakdown Voltage	$I_f = 10$ μ A	5	30		V
λ_p	Peak Wavelength	$I_f = 20$ mA	865	880	895	nm
$\Delta\lambda$	Spectral Bandwidth @ 50% (FWHM)	$I_f = 20$ mA		65		nm
C_t	Terminal Capacitance	$V_r = 0$ V, $f = 1$ MHz		15		pF
t_r	Rise Time	$I_f = 20$ mA		0.75		μ S
t_f	Fall Time	$I_f = 20$ mA		0.40		μ S

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